

isc Silicon NPN Power Transistor

2SD1691

DESCRIPTION

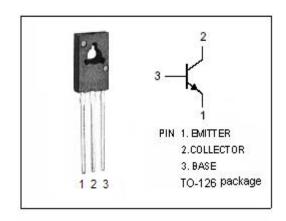
- High Collector Current -I_C= 5A
- · Low Collector Saturation Voltage
 - : V_{CE(sat)}= 0.3V(Max.)@ I_C= 2A
- · Complement to Type 2SB1151
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

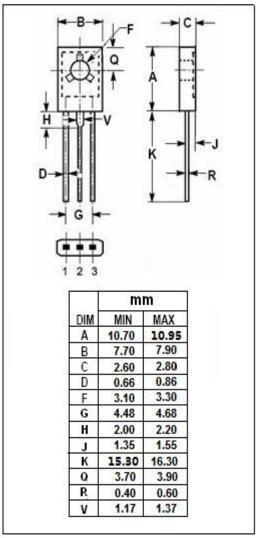
APPLICATIONS

 Designed for use in DC-DC converter, or driver of solenoid or motor.



| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------|------------|--|
| V _{CBO} | Collector-Base Voltage | 60 | V | |
| Vceo | Collector-Emitter Voltage | 60 | V | |
| V _{EBO} | Emitter-Base Voltage | 7 | V | |
| Ic | Collector Current-Continuous | 5 | Α | |
| I _{CP} | Collector Current-Pulse | 8 | Α | |
| I _B | Base Current-Continuous | 1 | Α | |
| Pc | Collector Power Dissipation @ Tc=25°C | 20 | W | |
| | Collector Power Dissipation @ T _a =25°C | 1.3 | | |
| TJ | Junction Temperature | 150 | $^{\circ}$ | |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ | |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | |
|----------------------|--------------------------------------|--|-----|------|-----|------------|--|
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 2A; I _B = 0.2A | | | 0.3 | V | |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 2A; I _B = 0.2A | | | 1.2 | V | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 50V; I _E = 0 | | | 10 | μ A | |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 7V; I _C = 0 | | | 10 | μ A | |
| h _{FE-1} | DC Current Gain | I _C = 0.1A; V _{CE} = 1V | 60 | | | | |
| h _{FE-2} | DC Current Gain | Ic= 2A; VcE= 1V | 100 | | 400 | | |
| h _{FE-3} | DC Current Gain | I _C = 5A; V _{CE} = 1V | 50 | | | | |
| Switching Times | | | | | | | |
| t _{on} | Turn-on Time | | | | 1.0 | μS | |
| t _{stg} | Storage Time | $I_{C}^{=}$ 2A, $I_{B1}^{=}$ $I_{B2}^{=}$ 0.2A; R _L = 5 Ω ; V_{CC}^{∞} 10V | | | 2.5 | μ s | |
| t _f | Fall Time | | | | 1.0 | μ \$ | |

h_{FE-2} Classifications

| M | L | К |
|---------|---------|---------|
| 100-200 | 160-320 | 200-400 |

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